### **60V N-Channel MOSFET**

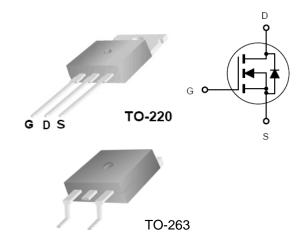
# **Applications:**

- Power Supply
- DC-DC Converters

$V_{ m DS}$	$R_{DS(ON)}(MAX)$	${ m I_D}^a$
60V	$6$ m $\Omega$	115A

#### **Features:**

- Lead Free
- Low R<sub>DS(ON)</sub> to Minimize Conductive Loss
- Low Gate Charge for Fast Switching Application
- Optimized V<sub>(BR)DSS</sub> Capability



Ordering Information

Park Number	Package	Brand
MXP6006DT	TO-220	MXP
MXP6006DF	TO-263	MXP

**Absolute Maximum Ratings** Tc=25°C unless otherwise specified

Symbol	Parameter	Value	Unit
$V_{ m DSS}$	Drain-to-Source Voltage	60	V
${\rm I_D}^a$	Continuous Drain Current	115	A
I <sub>DM</sub>	Pulsed Drain Current @V <sub>G</sub> =10V	459	A
$P_{\mathrm{D}}$	Power Dissipation	158	W
PD	Derating Factor above 25℃	1.05	W/°C
$V_{GS}$	Gate-to-Source Voltage	+/-20	V
Eas	Single Pulse Avalanche Energy (L=1mH)	449	mJ
Ias	Pulsed Avalanche Energy	Figure 9	A
$T_{\rm j}$ and $T_{\rm stg}$	Operating Junction and Storage Temperature Range	-55 to 175	$^{\circ}\!\mathbb{C}$

**Thermal Resistance** 

I II CI III di	resistance					
Symbol	Parameter	Min	Тур	Max	Unit	Test Conditions
$R_{ heta  ext{IC}}$	Junction-to-Case	-	-	0.95	°C/W	Water cooled heatsink, P <sub>D</sub> adjusted for a peak junction Temperature of 175°C

Note:

a: Calculated continuous current based upon maximum allowable junction temperature +175 °C. Package limitation current is 80A.

# **OFF** Characteristics

T<sub>2</sub>=25°C unless otherwise specified

Symbol	Parameter	Min	Тур	Max	Unit	Test Conditions
$V_{\left( \mathrm{BR}\right) \mathrm{DSS}}$	Drain-to-Source Breakdown Voltage	60	-	1	V	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA
Idss	Drain-to-Source Leakage Current	1	-	1	uA	$V_{DS}=48V, V_{GS}=0V$
		ı	-	100		$V_{DS}$ =48V, $V_{GS}$ =0V, $T_{J}$ =125 $^{\circ}$ C
ī	Gate-to-Source Forward Leakage	-	-	100		$V_{GS}=+20V$
Igss	Gate-to-Source Reverse Leakage	-	-	100	nA	$V_{GS}$ = -20 $V$

### **ON** Characteristics

T<sub>3</sub>=25°C unless otherwise specified

Symbol	Parameter	Min	Тур	Max	Unit	Test Conditions
Rds(on)	Static Drain-to-Source On-Resistance	1	4.6	6.0	mΩ	$V_{GS}=10V, I_{D}=24A$
$V_{\text{GS(th)}}$	Gate Threshold Voltage.	2	-	4	V	$V_{GS}=V_{DS}$ , $I_D=250uA$

**Dynamic Characteristics** 

Essentially independent of operating temperature

Dynami	C Characteristics	Essemuan	y macpena	ciit or opci	ating ici	inperature
Symbol	Parameter	Min	Тур	Max	Unit	Test Conditions
Ciss	Input Capacitance	-	5117	1	pF	N. ON N. OSN
Coss	Output Capacitance	-	534	1		$V_{GS}=0V, V_{DS}=25V, f=1.0MHz$
Crss	Reverse Transfer Capacitance	-	185	-		1-1.01VII1Z
Qg	Total Gate Charge	-	68	-		
Qgs	Gate-to-Source Charge	-	25	-	пC	$V_{DD}$ =30V, $I_D$ =57A, $V_{GS}$ =10V
Qgd	Gate-to-Drain ("Miller") Charge	-	16	-		
Td(on)	Turn-on Delay Time	-	18	1		
Tr	Rise Time	-	43	-	nS	VDD=30V, ID=57A,
Td(off)	Turn-off Delay Time	-	46	-		$V_G=10V, R_G=2.5\Omega$
Tf	Fall Time	-	13	-		

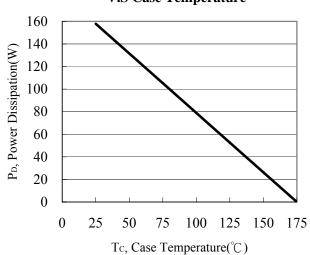
Source-Drain Diode Characteristics T=25°C unless otherwise specified

Symbol	Parameter	Min	Тур	Max	Unit	Test Conditions
$V_{ ext{SD}}$	Diode Forward Voltage	-	-	1.2	V	$I_S=24A, V_{GS}=0V$
Trr	Reverse Recovery Time	-	1	108.3	nS	Ig=28 A di/dt=100 A /ug
Orr	Reverse Recovery Charge	-	-	85.4	nC	Is=38A, $di/dt=100A/\mu s$

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Figure 1. Maximum Power Dissipation V.S Case Temperature



**Current V.S Case Temperature** 

Figure 2. Maximum Continuous Drain

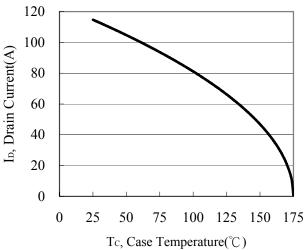


Figure 3. Typical Output Characteristics

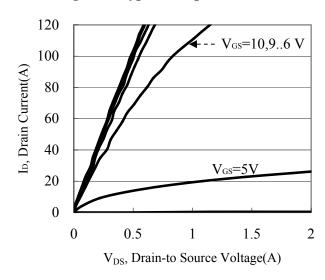


Figure 4. Breakdown Voltage V.S Junction Temperature

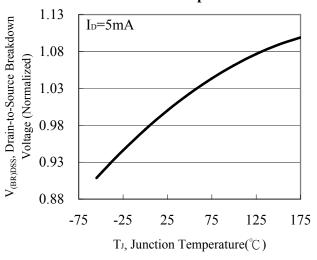


Figure 5. Threshold Voltage V.S Junction Temperature

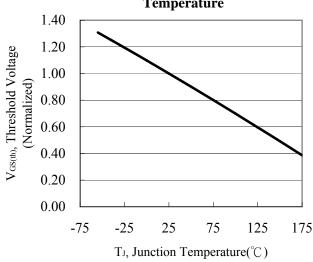


Figure 6. Drain-to-Source Resistance V.S Junction Temperature

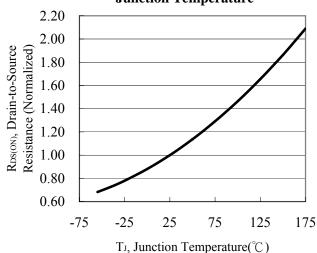


Figure 7. Typical Gate Charge vs. Gate-

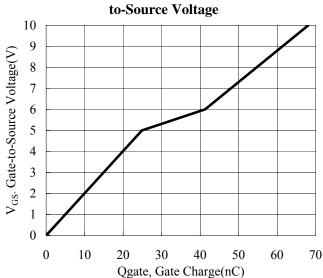


Figure 8. Typical Capacitance vs. Drain-

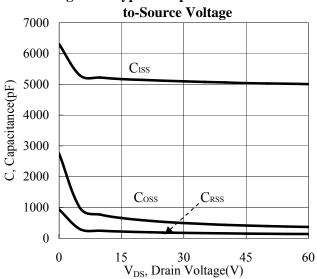


Figure 9. Unclamped Inductive Switching Canability

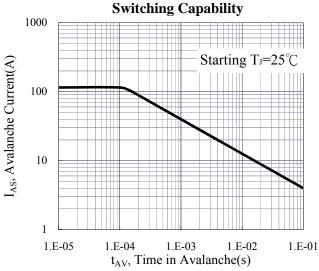
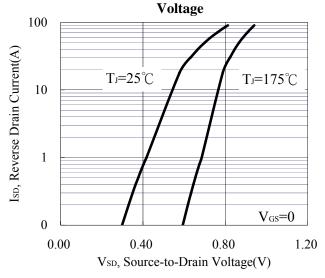


Figure 10. Source-Drain Diode Forward



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